

Silicon PNP Power Transistors

2SA1294

DESCRIPTION

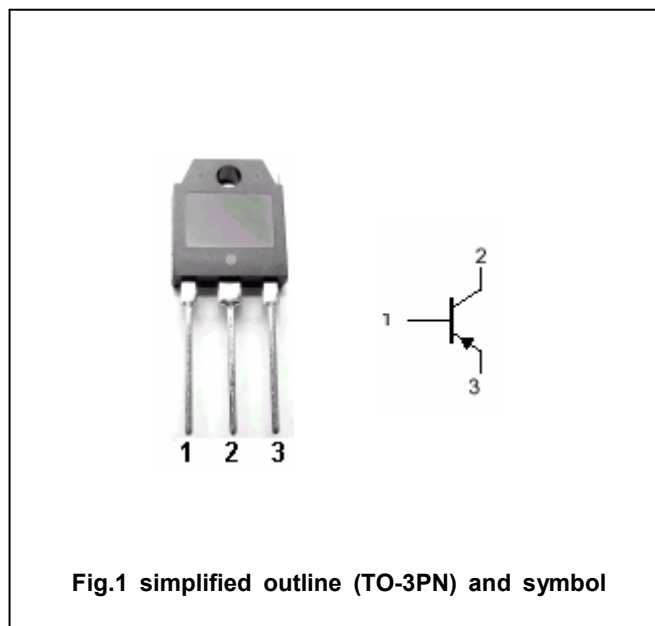
- With TO-3PN package
- Complement to type 2SC3263

APPLICATIONS

- Audio and general purpose

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

**Absolute maximum ratings(Ta=□)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-230	V
V_{CEO}	Collector-emitter voltage	Open base	-230	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-15	A
I_B	Base current		-4	A
P_C	Collector power dissipation	$T_C=25^\circ$	130	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEO}	Collector-emitter breakdown voltage	$I_C=-25mA$; $I_B=0$	-230			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-5A$; $I_B=-0.5A$			-2.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=-230V$; $I_E=0$			-100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-5V$; $I_C=0$			-100	μA
h_{FE}	DC current gain	$I_C=-5A$; $V_{CE}=4V$	50		140	
C_{ob}	Output capacitance	$I_E=0$; $V_{CB}=-10V$; $f=1MHz$		500		pF
f_T	Transition frequency	$I_E=2A$; $V_{CE}=-12V$		35		MHz

Switching times

t_{on}	Turn-on time	$I_C=-5A$; $R_L=12\Omega$ $I_{B1}=-I_{B2}=-0.5A$ $V_{CC}=-60V$		0.35		μs
t_s	Storage time			1.5		μs
t_f	Fall time			0.3		μs

◆ h_{FE} Classifications

O	Y
50-100	70-140

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[illegible]

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)

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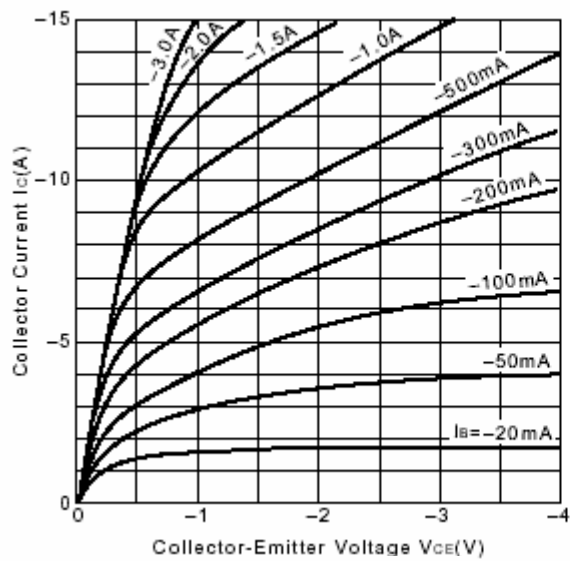


Fig.3 Static Characteristic

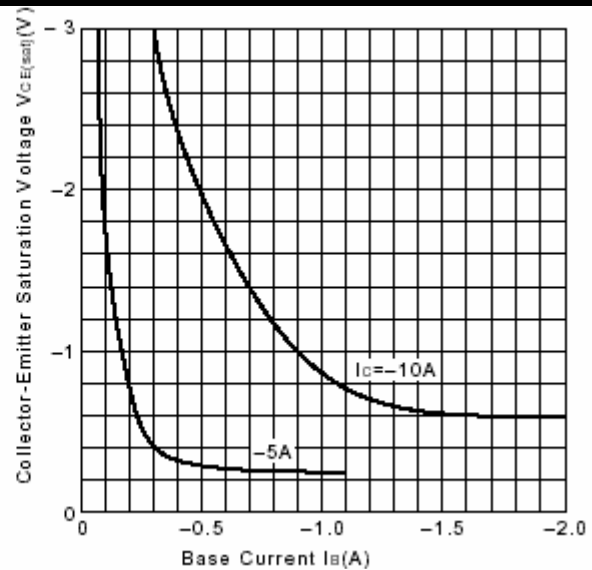
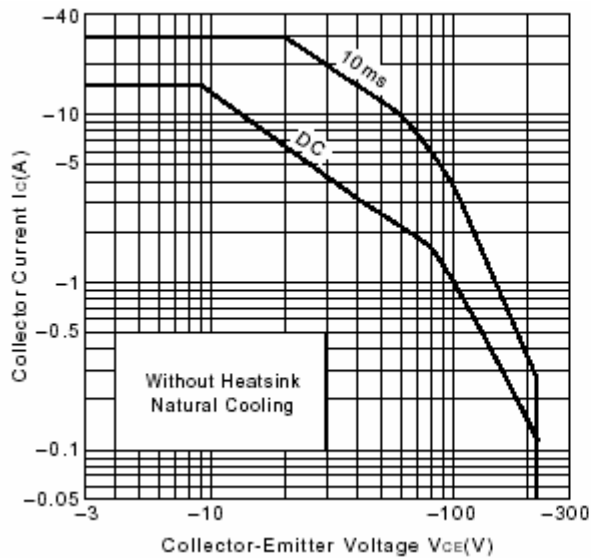
Fig.4 $V_{CE(sat)}$ - I_B Characteristics

Fig.5 Safe Operating Area

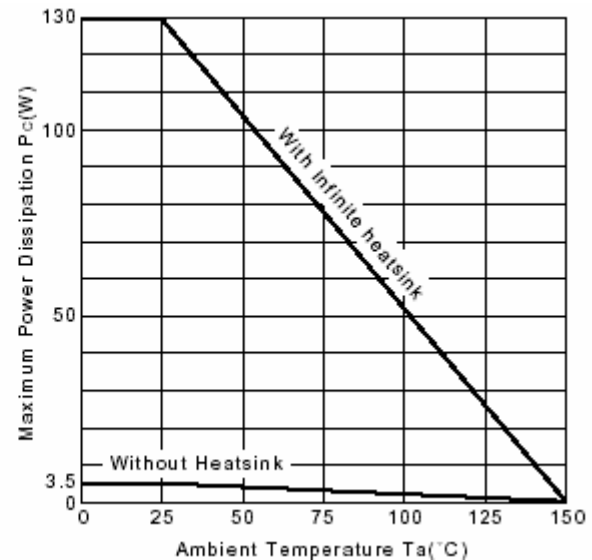
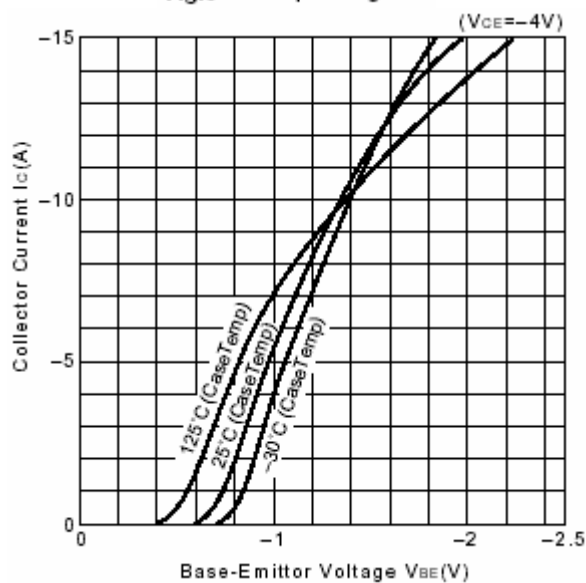
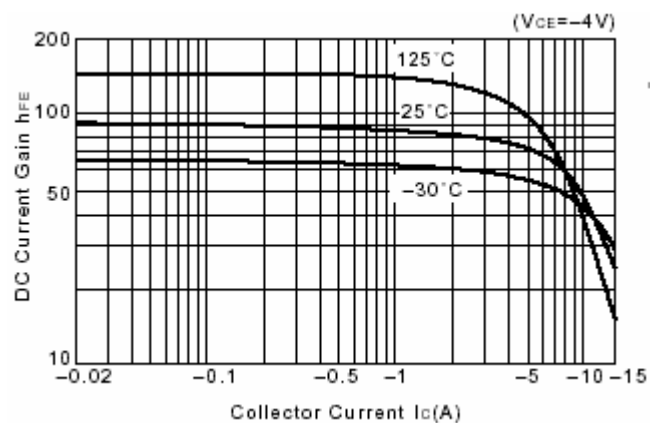
Fig.6 P_C - T_a DeratingFig.7 I_C - V_{BE} 

Fig.8 DC current Gain